

# Low-Input-Current **Operational Amplifier**

# **PM108**

### 1.0 **SCOPE**

This specification documents the detailed requirements for Analog Devices space qualified die including die qualification as described for Class K in MIL-PRF-38534, Appendix C, Table C-II except as modified herein.

The manufacturing flow described in the STANDARD DIE PRODUCTS PROGRAM brochure at http://www.analog.com/marketSolutions/militaryAerospace/pdf/Die\_Broc.pdf is to be considered a part of this specification.

This data sheet specifically details the space grade version of this product. A more detailed operational description and a complete data sheet for commercial product grades can be found at www.analog.com/PM108

#### 2.0 Part Number. The complete part number(s) of this specification follow:

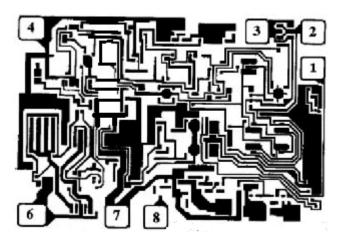
Part Number	Description
PM108-000C	Low-Input-Current Operational Amplifier
PM108R000C	Radiation tested Low-Input-Current Operational Amplifier

#### 3.0 **Die Information**

#### 3.1 **Die Dimensions**

Die Size	Die Thickness	Bond Pad Metalization
54 mil x 74 mil	19 mil ± 2 mil	Al/Cu

#### 3.2 **Die Picture**



- 1. COMP
- 2. -IN
- 3. +IN
- 4. V-
- 5. NC
- OUT 6.
- 7. V+
- COMP 8.

### ASD0012750

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### 3.3 Absolute Maximum Ratings 1/

Supply Voltage (Vcc)	<u>+</u> 22 V
Input Voltage (V <sub>IN</sub> ) <u>2/</u>	±15 V
Differential Input Current <u>3/</u>	±10 mA
Output Short-Circuit Duration	Indefinite
Storage Temperature Range	
Junction Temperature (T <sub>J</sub> )	+175 °C
Ambient Temperature Range	
Absolute Maximum Ratings Notes:	

<sup>1/</sup> Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

2/ For supply voltages less than ±15 V, the absolute maximum input voltage is equal to the supply voltage.

<u>3/</u> The inputs are shunted with back-to-back diodes for overvoltage protection. Therefore, if a differential input voltage in excess of 1 V is applied between the inputs, excessive current will flow, unless some limiting resistance is provided.

### 4.0 Die Qualification

In accordance with class-K version of MIL-PRF-38534, Appendix C, Table C-II,

- except as modified herein.
- (a) Qual Sample Size and Qual Acceptance Criteria 10/0
- (b) Qual Sample Package DIP
- (c) Pre-screen electrical test over temperature performed post-assembly prior to die qualification.

### Table I Notes:

Table I - Dice Electrical Characteristics							
Parameter	Symbol	Limit Min	Limit Max	Units			
Input Offset Voltage	V <sub>IO</sub>		-0.5	0.5	mV		
Input Offset Current	lıo		-0.2	0.2	nA		
Input Bias Current	±І <sub>ІВ</sub>		-0.1	2	nA		
	+PSRR	+V <sub>CC</sub> = +10 V to +20 V, -V <sub>CC</sub> = -20 V	-16	16			
Power Supply Rejection Ratio	-PSRR	$+V_{cc} = +20 V$ , $-V_{cc} = -10 V$ to $-20 V$	-16	16	μV/V		
Input Voltage Range	IVR		±15		V		
Input Voltage Common Mode Rejection	CMR	$V_{CM} = IVR$	96		dB		
Supply Current	Icc	$\pm V_{CC} = \pm 15 V$		0.6	mA		
Output Voltage Swing	±V <sub>OP</sub>	$\pm V_{CC} = \pm 20 \text{ V}, \text{ R}_{L} = 10 \text{ k}\Omega$	±16		V		
Open Loop Voltage Gain	Avs	$ \pm V_{CC} = \pm 15 \text{ V}, \text{ R}_{\text{L}} = 10 \text{ k}\Omega $ $ V_{\text{OUT}} = \pm 10 \text{ V} $	80		V/mV		

Table I Notes:

 $\underline{1/}$  V\_{CC} = ±20 V, R\_{S} = 50  $\Omega,$  V\_{CM} = 0 V, and T\_{A} = 25 °C, unless otherwise specified.

Table II - Electrical Characteristics for Qual Samples								
Parameter	Symbol	Conditions <u>1/3</u> /		Sub- groups	Limit Min	Limit Max	Units	
				1	-0.5	0.5		
Input Offset Voltage <u>3</u> /	VIO			2, 3	-1	1	mV	
			M, D, L, R	1	-2	2		
				1	-0.2	0.2	1	
Input Offset Current <u>3</u> /	lio			2, 3	-0.4	0.4		
			M, D, L, R	1	-1	1		
				1	-0.1	2	2 nA	
Input Bias Current <u>3</u> /	±I <sub>IB</sub>			2, 3	-0.4	0.4		
			M, D, L, R	1	-25	25		
Input Offset Voltage Temperature Sensitivity <u>2</u> /	$\Delta V_{IO} / \Delta T$			2, 3	-5	5	µV/°C	
	Vvs	±V <sub>CC</sub> = ±15 V, R <sub>L</sub> = 10 KΩ,		4	80			
Open Loop Voltage Gain <u>3</u> /		V <sub>OUT</sub> =	±10 V	5,6	40		V/mV	
			M, D, L, R	4	10			
Power Supply Principal Datio 2/	+PSRR		V to +20 V -20 V	1, 2, 3	-16	16		
Power Supply Rejection Ratio <u>2</u> /	-PSRR	$+V_{CC} = +20 V$ $-V_{CC} = -10 V \text{ to } -20 V$		1, 2, 3	-16	16	μV/V	
Input Voltage Range <u>2</u> /	IVR			1, 2, 3	±15		V	
Supply Current <u>2</u> /	Icc	$V_{CC} = \pm 15 V$		1, 2		0.6	mA	
Supply Current <u>2</u> /				3		0.8		
Input Voltage Common Mode Rejection Ratio <u>2</u> /	CMRR	$V_{CM} = IVR$		1, 2, 3	96		dB	
Output Short-Circuit Current <u>2</u> /	I <sub>OS(+)</sub> I <sub>OS(-)</sub>	$\pm V_{CC} = \pm 15 \text{ V}, t \le 25 \text{ mS}$		1	-15	15	mA	
Output Voltage Swing 2/	±V <sub>OP</sub>	$\pm V_{CC}$ = $\pm 20$ V, R <sub>L</sub> = 10 K $\Omega$		4, 5, 6	±16		V	

 Table II Notes:

 1/2  $V_{CC} = \pm 20$  V,  $R_S = 50 \Omega$ , and  $V_{CM} = 0$  V, unless otherwise specified.

 2/2 Not tested post-irradiation

 3/2 Irradiated at dose rate = 50 - 300 rads (Si)/s in accordance with MIL

 400 Intradiated at dose rate = 50 - 300 rads (Si)/s in accordance with MIL

Irradiated at dose rate = 50 - 300 rads (Si)/s in accordance with MIL-STD-883, method 1019, condition A, and is guaranteed to a maximum total dose specified of 100 krad (Si). The effective dose rate after extended room temperature anneal = 1.15 rad (Si)/s per MIL-STD-883, method 1019, condition A, section 3.11.2. The total dose specification for this device only applies to the specified effective dose rate, or lower, environment.

Table III - Life Test Endpoint and Delta Parameter (Product is tested in accordance with Table II with the following exceptions)								
Parameter	Symbol	Sub- groups	Post Burn-in Limit		Post Life Test Limit		Life Test	Units
			Min	Max	Min	Max	Delta	Onits
In rout Offerst Vielte ro	oltage V <sub>io</sub>	1		±0.75		±1	±0.25	
Input Offset Voltage		2, 3				±1.5		mV
Input Bias Current	±Іıв	1	-0.1	2.5	-0.1	±3	±0.5	
		2			-1	±3		nA
		3			-0.1	±4		
Input Offset Current	lıo	1		±0.3		±0.3		
		2, 3				±0.5		nA

## 5.0 Life Test/Burn-In Information

- 5.1 HTRB is not applicable for this drawing.
- 5.2 Burn-in is per MIL-STD-883 Method 1015 test condition B or C.
- 5.3 Steady state life test is per MIL-STD-883 Method 1005.

Rev	Description of Change	Date
А	Initiate	7-Feb-02
В	Add radiation test limits. Update web address.	9-Jan-03
C	Make correction file names (see OP215)	9-Jan-03
D	Update 1.0 Scope description.	09-Jul-07
E	Update header/footer & add to 1.0 scope description.	19-Feb-08
F	Add Junction Temperature(T <sub>J</sub> )175°C to 3.3 Absolute Maximum Ratings	March 31, 2008
G	Updated Section 4.0c note to indicate pre-screen temp testing being performed.	6-JUN-2009
Н	Update fonts and sizes to ADI standard	3-Oct-2011
I	Add dose rate environment at Table II Notes.	08-Jun-21

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